

# NVATS68301PZ

## Power MOSFET

–100 V, 75 mΩ, –31 A, P-Channel



ON Semiconductor®

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The NVATS68301PZ is a power MOSFET designed for compact size and high efficiency which can achieve high thermal performance. AEC-Q101 qualified MOSFET and PPAP capable suitable for automotive applications.

### Features

- Low On-Resistance
- High Current Capability
- 100% Avalanche Tested
- AEC-Q101 qualified and PPAP capable
- ATPAK package is pin-compatible with DPAK (TO-252)
- Pb-Free, Halogen Free and RoHS compliance

### Typical Applications

- Reverse Battery Protection
- Load Switch
- Automotive Front Lighting
- Automotive Body Controllers

### SPECIFICATIONS

ABSOLUTE MAXIMUM RATING at Ta = 25°C (Note 1)

| Parameter                                            | Symbol                            | Value       | Unit |
|------------------------------------------------------|-----------------------------------|-------------|------|
| Drain to Source Voltage                              | V <sub>DSS</sub>                  | –100        | V    |
| Gate to Source Voltage                               | V <sub>GSS</sub>                  | ±20         | V    |
| Drain Current (DC)                                   | I <sub>D</sub>                    | –31         | A    |
| Drain Current (Pulse)<br>PW ≤ 10 μs, duty cycle ≤ 1% | I <sub>DP</sub>                   | –124        | A    |
| Power Dissipation<br>Tc=25°C                         | P <sub>D</sub>                    | 84          | W    |
| Operating Junction and<br>Storage Temperature        | T <sub>J</sub> , T <sub>stg</sub> | –55 to +175 | °C   |
| Avalanche Energy (Single Pulse) (Note 2)             | E <sub>AS</sub>                   | 54          | mJ   |
| Avalanche Current (Note 3)                           | I <sub>AV</sub>                   | –28         | A    |

Note 1 : Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

2 : V<sub>DD</sub> = –30 V, L = 100 μH, I<sub>AV</sub> = –28 A (Fig.1)

3 : L ≤ 100 μH, Single pulse

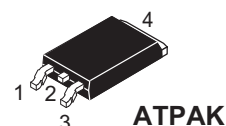
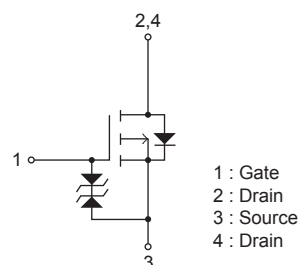
### THERMAL RESISTANCE RATINGS

| Parameter                                 | Symbol           | Value | Unit |
|-------------------------------------------|------------------|-------|------|
| Junction to Case Steady State (Tc = 25°C) | R <sub>θJC</sub> | 1.78  | °C/W |
| Junction to Ambient (Note 4)              | R <sub>θJA</sub> | 79.3  | °C/W |

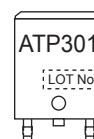
Note 4 : Surface mounted on FR4 board using a 130 mm<sup>2</sup>, 1 oz. Cu pad

| V <sub>DSS</sub> | R <sub>DS(on)</sub> Max | I <sub>D</sub> Max |
|------------------|-------------------------|--------------------|
| –100 V           | 75 mΩ @ –10 V           | –31 A              |

### ELECTRICAL CONNECTION P-Channel



### MARKING



### ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

# NVATS68301PZ

## ELECTRICAL CHARACTERISTICS at Ta = 25°C (Note 5)

| Parameter                                  | Symbol        | Conditions                                                                  | Value |       |          | Unit             |
|--------------------------------------------|---------------|-----------------------------------------------------------------------------|-------|-------|----------|------------------|
|                                            |               |                                                                             | min   | typ   | max      |                  |
| Drain to Source Breakdown Voltage          | $V_{(BR)DSS}$ | $I_D = -1 \text{ mA}$ , $V_{GS} = 0 \text{ V}$                              | -100  |       |          | V                |
| Zero-Gate Voltage Drain Current            | $I_{DSS}$     | $V_{DS} = -100 \text{ V}$ , $V_{GS} = 0 \text{ V}$                          |       |       | -1       | $\mu\text{A}$    |
| Gate to Source Leakage Current             | $I_{GSS}$     | $V_{GS} = \pm 16 \text{ V}$ , $V_{DS} = 0 \text{ V}$                        |       |       | $\pm 10$ | $\mu\text{A}$    |
| Gate Threshold Voltage                     | $V_{GS(th)}$  | $V_{DS} = -10 \text{ V}$ , $I_D = -1 \text{ mA}$                            | -2.0  |       | -3.5     | V                |
| Forward Transconductance                   | $g_{FS}$      | $V_{DS} = -10 \text{ V}$ , $I_D = -14 \text{ A}$                            |       | 29    |          | S                |
| Static Drain to Source On-State Resistance | $R_{DS(on)}$  | $I_D = -14 \text{ A}$ , $V_{GS} = -10 \text{ V}$                            |       | 57    | 75       | $\text{m}\Omega$ |
| Input Capacitance                          | $C_{iss}$     | $V_{DS} = -20 \text{ V}$ , $f = 1 \text{ MHz}$                              |       | 2,850 |          | pF               |
| Output Capacitance                         | $C_{oss}$     |                                                                             |       | 270   |          | pF               |
| Reverse Transfer Capacitance               | $C_{rss}$     |                                                                             |       | 125   |          | pF               |
| Turn-ON Delay Time                         | $t_{d(on)}$   | See Fig.2                                                                   |       | 26    |          | ns               |
| Rise Time                                  | $t_r$         |                                                                             |       | 150   |          | ns               |
| Turn-OFF Delay Time                        | $t_{d(off)}$  |                                                                             |       | 250   |          | ns               |
| Fall Time                                  | $t_f$         |                                                                             |       | 170   |          | ns               |
| Total Gate Charge                          | $Q_g$         | $V_{DS} = -60 \text{ V}$ , $V_{GS} = -10 \text{ V}$ , $I_D = -28 \text{ A}$ |       | 55    |          | nC               |
| Gate to Source Charge                      | $Q_{gs}$      |                                                                             |       | 10    |          | nC               |
| Gate to Drain "Miller" Charge              | $Q_{gd}$      |                                                                             |       | 17    |          | nC               |
| Forward Diode Voltage                      | $V_{SD}$      | $I_S = -28 \text{ A}$ , $V_{GS} = 0 \text{ V}$                              |       | -0.88 | -1.5     | V                |

Note 5 : Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted.  
Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Fig.1 Unclamped Inductive Switching Test Circuit

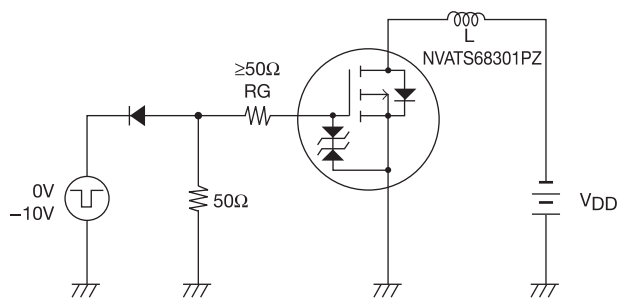
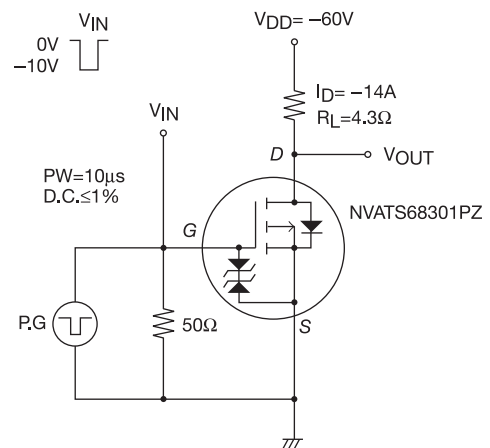
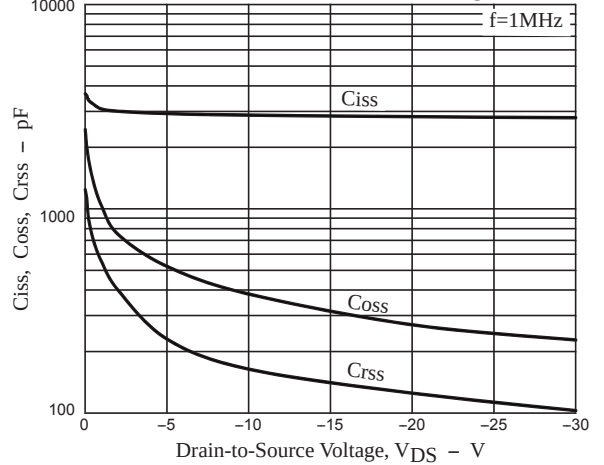
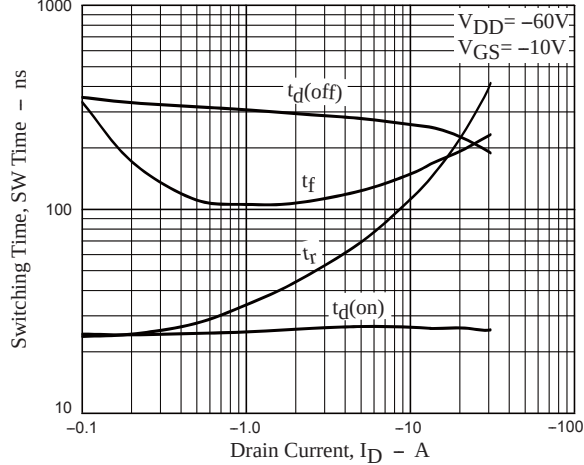
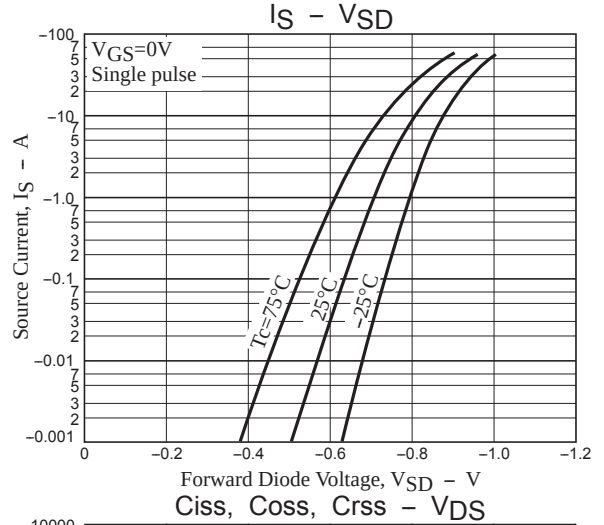
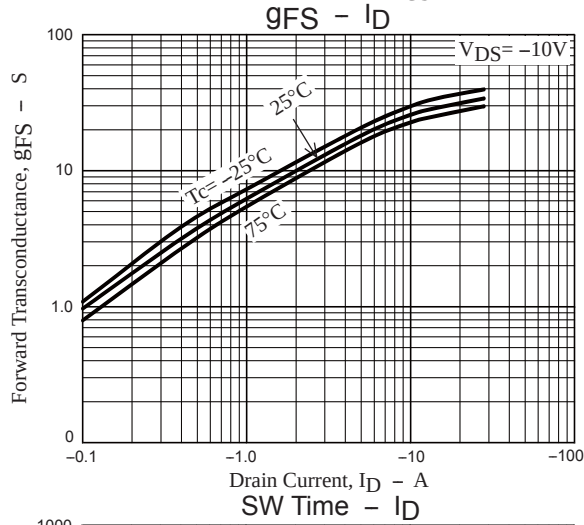
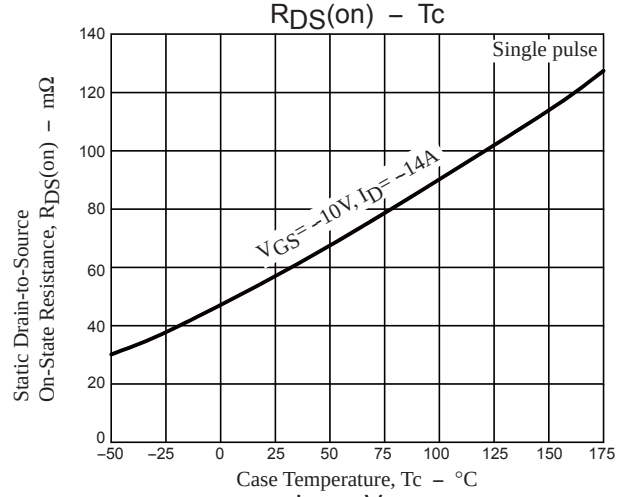
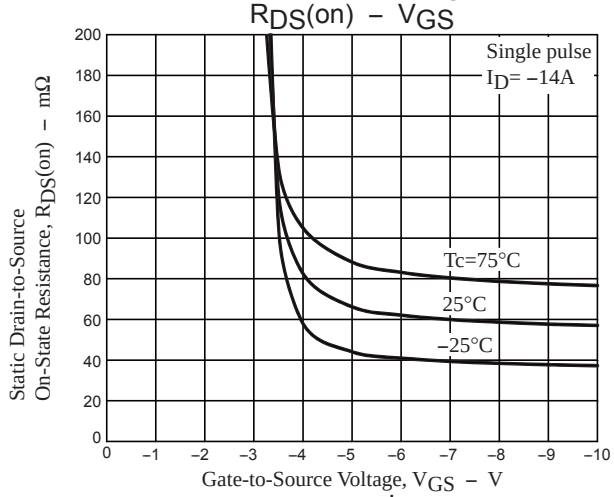
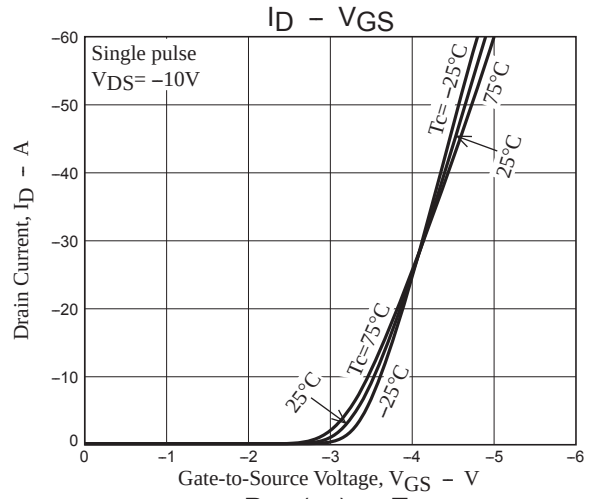
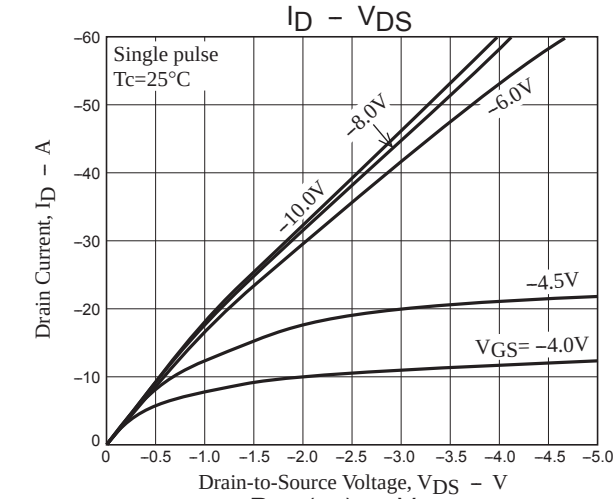


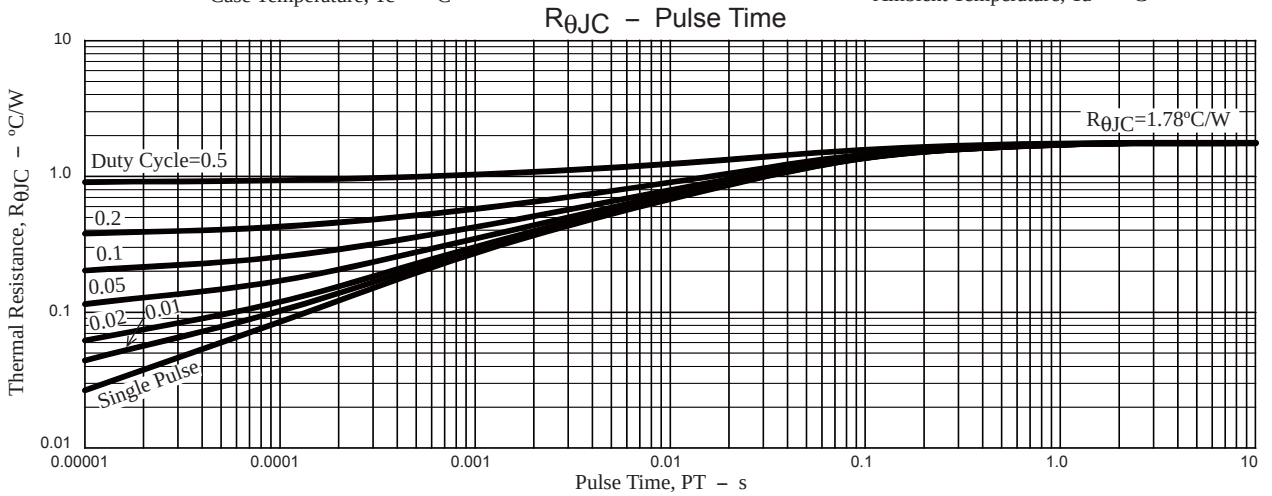
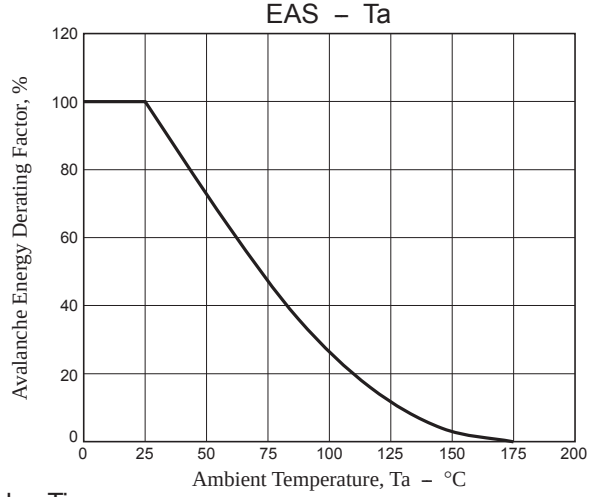
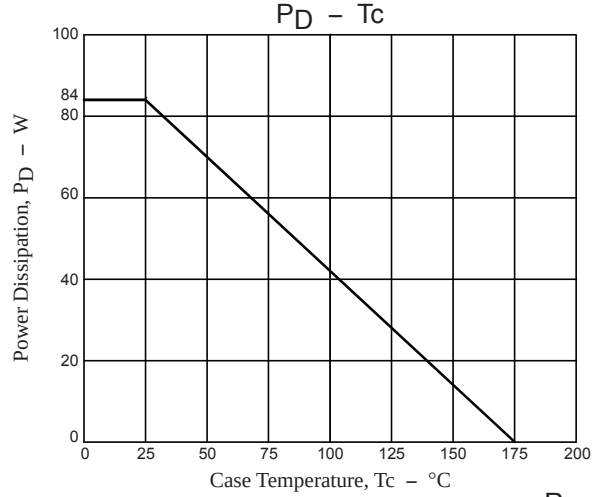
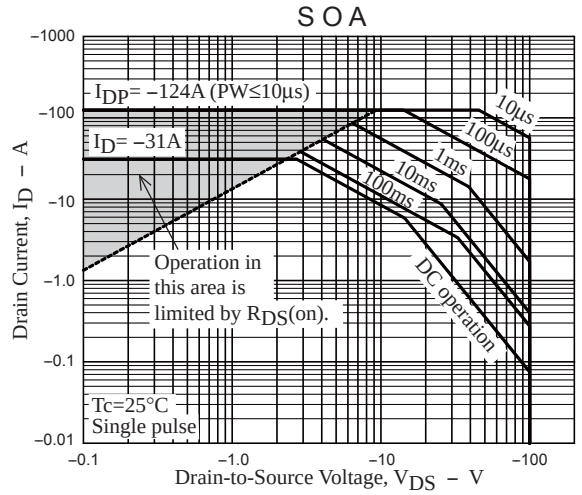
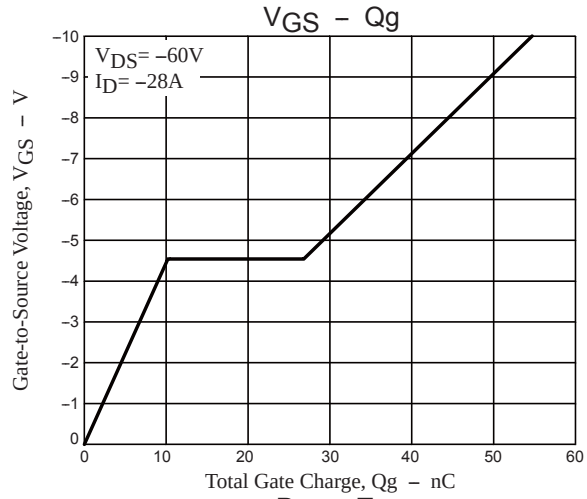
Fig.2 Switching Time Test Circuit



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# NVATS68301PZ



**NVATS68301PZ**

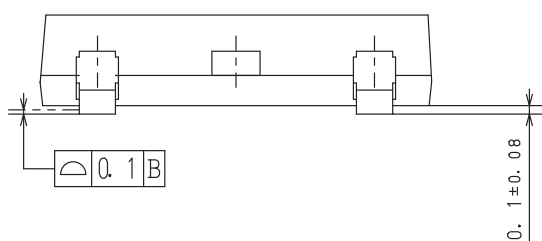
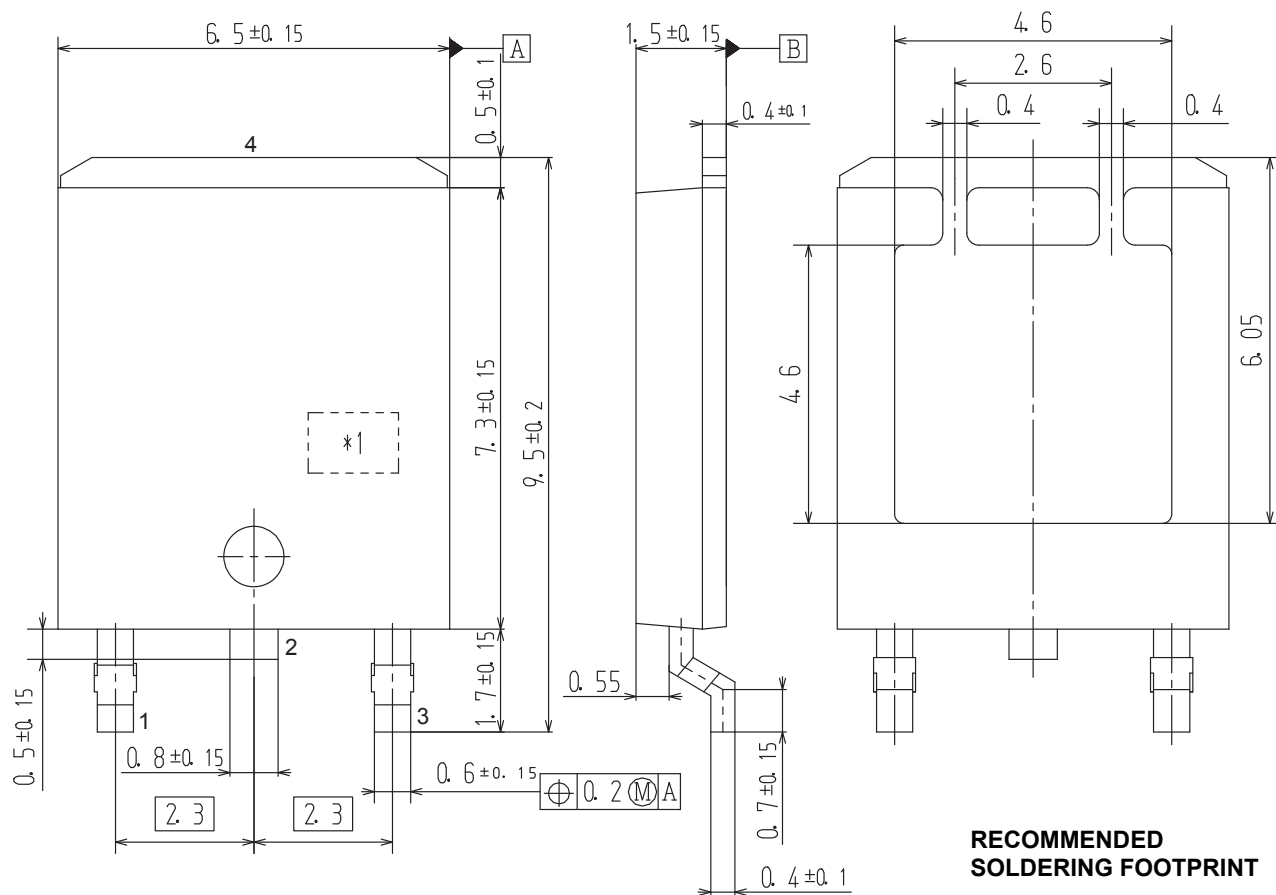
## PACKAGE DIMENSIONS

unit : mm

### DPAK (Single Gauge) / ATPAK

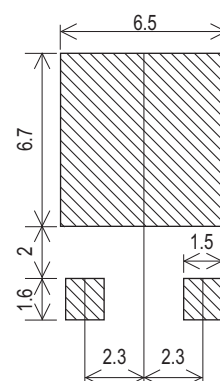
CASE 369AM

ISSUE 0



Pin2 is idle pin with electrical designation only carried

\*1: Lot indication



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## ORDERING INFORMATION

| Device          | Marking | Package                                                | Shipping (Qty / Packing) |
|-----------------|---------|--------------------------------------------------------|--------------------------|
| NVATS68301PZT4G | ATP301  | DPAK(Single Gauge) / ATPAK<br>(Pb-Free / Halogen Free) | 3,000 / Tape & Reel      |

† For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. [http://www.onsemi.com/pub\\_link/Collateral/BRD8011-D.PDF](http://www.onsemi.com/pub_link/Collateral/BRD8011-D.PDF)

Note on usage : Since the NVATS68301PZ is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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#### Как с нами связаться

**Телефон:** 8 (812) 309 58 32 (многоканальный)

**Факс:** 8 (812) 320-02-42

**Электронная почта:** [org@eplast1.ru](mailto:org@eplast1.ru)

**Адрес:** 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.